

ANALOG DELAY CIRCUIT**BACKGROUND OF THE INVENTION****1. Field of the Invention**

This invention relates to an analog delay circuit and a clock generation circuit for use with an analog delay circuit, and more particularly to an analog delay circuit which delays an analog signal by repetitively performing writing/reading of information in a predetermined write/read cycle into and from memory capacitors of memory cells arranged two-dimensionally in a matrix and a clock generation circuit for use with an analog delay circuit.

2. Description of the Related Arts

A delay circuit for an analog signal is required to delay a color signal by 1 H (horizontal sweep period), for example, in a color signal demodulation circuit of a color television receiver of the PAL (Phase Alternation by Line) system. In particular, in the PAL system, since a modulated signal from two color signals is transmitted reversing the polarity thereof for each one scanning line, the color signal demodulation circuit requires a 1 H delay time in order to establish line correlation. The analog

delay circuit has, for example, such a circuit construction as shown in FIG. 1.

Referring to FIG. 1, a write switch S1 and a read switch S2 are connected in series between a circuit input terminal 6 and the inverting (-) input terminal of an operational amplifier A1. The non-inverting (+) input terminal of the operational amplifier A1 is grounded, and the output terminal of the operational amplifier A1 is connected to a circuit output terminal 7, and a read capacitor Co and a reset switch S3 are connected in parallel between the inverting input terminal and the output terminal of the operational amplifier A1. Further, N selection switches S(N) and N memory capacitors C(n) are connected between a junction P of the switches S1 and S2 and the ground.

FIG. 2 is a timing chart of operations of the switches S1 to S3. Referring to FIG. 2, within a period T1, the write switch S1 and the reset switch S3 are open and the read switch S2 is closed, and consequently, charge of the nth memory capacitor C(n) is transferred to the read capacitor Co. The charge in this instance is charge which was written prior by one cycle (N clocks). Within another

period T_2 , the read switch S_2 is open and the write switch S_1 and the reset switch S_3 are closed. The write switch S_1 writes an input signal to the circuit input terminal 6 into the memory capacitors $C(n)$, and the reset switch S_3 resets the read capacitor C_0 . Similarly, within a further period T_3 , charge of the memory capacitor $C(n+1)$ is read out, and within a still further period T_4 , the input signal is written.

FIG. 3 is a diagrammatic view of the concept of an analog delay. Referring to FIG. 3, n memory capacitors C_n are arranged, and information written in the last cycle into the i th memory capacitor C_i is read out and then information in the present cycle is written into the memory capacitor C_i . Such operation is successively performed for $C_i \rightarrow C_{i+1} \rightarrow \dots \rightarrow C_n$ and then for C_1 . Here, if the read/write cycle is represented by T , a delay of nT is produced between the written information and the read information. Therefore, a delay circuit for an analog signal can be realized.

FIG. 4 is a circuit diagram showing a detailed construction of an analog value memory circuit which includes memory capacitors $C(n)$ and selection switches

S(N). Referring to FIG. 4, memory cells formed from selection switches S_{mn} and memory capacitors C_{mn} connected in series between row lines RL_n and the ground are arranged in a matrix of u columns and v rows. The selection switches S_{11} to S_{u1} , S_{12} to S_{u2} , ..., and S_{1v} to S_{uv} of the $u \cdot v$ memory cells are selectively controlled by column selection signals X_1 to X_u outputted from an X direction scanning circuit 11 and row selection signals Y_1 to Y_v outputted from a Y direction scanning circuit 12.

Those selection switches S_{11} to S_{u1} , S_{12} to S_{u2} , ..., S_{1v} to S_{uv} can be formed from MOSFETs, JFETs (junction type FETs) or bipolar transistors. A construction of memory cells of i columns and j rows where, for example, MOSFETs are used for the selection switches is shown in FIG. 5. Referring to FIG. 5, the anode of a diode D_{ij} and a terminal of a resistor R_{ij} are connected to the gate electrode of a MOSFET Q_{ij} serving as a selection switch. A column selection signal X_i is applied to the other terminal of the resistor R_{ij} and a row selection signal Y_j is applied to the cathode of the diode D_{ij} , and only when both of the column selection signal X_i and the row selection signal Y_j have a high potential, read/write from/into the

memory cell C_{ij} is enabled.

Operation waveforms of the circuit of FIG. 4 are shown in FIG. 6. Referring to FIG. 6, XCLK denotes a clock signal to be inputted to the X direction scanning circuit 11, YCLK denotes a clock signal to be inputted to the Y direction scanning circuit 12, X_1 to X_u denote column selection signals, and Y_1 to Y_3 denote row selection signals. It is to be noted that the clock signal YCLK has a period equal to u times that of the clock signal XCLK, and within one cycle of the clock signal YCLK, reading/writing is performed from the first to the n th columns. After the one period comes to an end, the row for reading/writing changes from the j th row to the $j+1$ th row, and then reading/writing is performed from the first to the u th columns similarly.

Here, operation for the j th row will be described with reference to a waveform diagram of FIG. 7. It is to be noted that enlarged waveforms of the row selection signal Y_j and the column selection signals X_1 , X_2 and X_u are shown in FIG. 7. First, for the memory cells in the first column, the column selection signal X_1 and the row selection signal Y_1 rise simultaneously. On the other

hand, for the memory cells in the u th column, the column selection signal X_u and the row selection signal Y_j fall simultaneously. For the memory cells in the second to $(u-1)$ th columns, the row selection signal Y_j is in a steady state, and a selection operation is performed only in response to the column selection signals X_2 to X_{u-1} .

In other words, the first column, the u th column and the other columns are driven in different conditions from one another. Accordingly, the gate electrode waveform of the MOSFET Q_{ij} as the selection switch shown in FIG. 5 is not exactly same among the first row, the u th row and the other rows. This is because the column selection signals X_1 to X_u and the row selection signals Y_1 to Y_v are delicately different in waveform or delay time and the diode D_{ij} and the resistor R_{ij} shown in FIG. 5 have parasitic capacitances and so forth.

FIG. 8 illustrates parasitic capacitances of a MOSFET in an example of the related arts wherein, for example, a MOSFET is used as a selection switch. Such parasitic capacitances C_{gs} , C_{gd} , C_{ss} and C_{ds} as seen in FIG. 8 are present between the source and drain which are poles of the switch and the gate and a substrate (or well).

Where those capacitances C_{gs} , C_{gd} , C_{ss} and C_{ds} are very small with a single switch, a total value of parasitic capacitances of 100 to 1,000 switches amounts to 10 times or occasionally to 100 times the memory capacitors $C(n)$. This problem similarly applies even where the switch element is formed from a JFET or a bipolar transistor although some difference is present in structure in which capacitances are formed.

Subsequently, it will be described what bad influence such parasitic capacitances have on operation of an analog delay circuit. The influence of the parasitic capacitances vary a little depending upon the structure of the analog delay circuit or the type of the switch elements, and this will be described below by way of an example of the circuit of FIG. 6. FIG. 9 shows an analog delay circuit which includes a single capacitor C_m and a single selection switch S_m in place of the N memory capacitors $C(n)$ and selection switches $S(N)$ of FIG. 6, respectively, and additionally includes a parasitic capacitance C_p .

The first problem resides in that, where a case wherein charge written in in the last cycle is read out is

considered, an input voltage written immediately prior to then is stored in the parasitic capacitance C_p . As a result, the charge read out to the read capacitor C_o is the sum of the original charge accumulated in the memory capacitor C_m and the charge accumulated in the parasitic capacitance C_p . The charge of the memory capacitor C_m has undergone a predetermined delay whereas the charge of the parasitic capacitance C_p has undergone little delay. Accordingly, the parasitic capacitance C_p gives rise to a side effect of leaking a signal free from a delay to the output.

One of possible countermeasures against the side effect is to control the individual switches at somewhat complicated timings. In particular, it is required to prevent the side effect described above by performing such complicated timing control as to set a time for discharging the charge of the parasitic capacitance C_p by closing the reset switch S_3 and the read switch S_2 before the charge of the memory capacitor C_m is read out.

Another problem, which is more fatal, resides in that the settling time of the output is extended. Where the band of the operational amplifier A_1 is represented by

ω_0 , the response time to a step input in a full feedback condition is $\tau = 1/\omega_0$. However, if the parasitic capacitance C_p is present, then the feedback ratio β is given by

$$\beta = 1/(1 + C_p/C_0) \quad \text{..... (1)}$$

Thus, the bandwidth of the loop decreases to $\beta\omega_0$ and also the time constant of the transient response changes to $\tau' = 1/\beta \cdot \tau$. Accordingly, if the capacitance value of the parasitic capacitance C_p is high, then this remarkably decreases the feedback ratio of the operational amplifier A1 when the charge accumulated in the memory capacitor C_m is read out, which makes high speed reading out difficult. In order to eliminate this, the band of the operational amplifier A1 should be designed to be very wide. This, however, is not practical.

In the analog delay circuit of the related art described above, when the memory cells of the matrix are scanned to select them, since such raster scanning as scanning of a television signal is performed as indicated by arrow marks in FIG. 10, where the gate electrode waveform of the MOSFET Q_{ij} is different among the first

column, the uth column and the other columns, the difference in gate electrode waveform appears as a difference in gain of the input/output characteristics in writing/reading or in offset characteristic via parasitic capacitances of the MOSFETs or arising from delicate differences in conducting state. Or in other words, there is a problem that noise of a fixed pattern is produced.

By the way, in such an application, as an application of an analog delay circuit, wherein an echo is applied, for example, to an audio signal, a high degree of accuracy is not required for the delay time. On the other hand, in a color signal demodulation circuit for a color television receiver of the PAL system, a delay time which conforms exactly with a horizontally synchronizing period is required. An example of a construction of a clock generation circuit in such an application as just described is shown in FIG. 11.

Referring to FIG. 11, the clock generation circuit shown has a PLL (Phase Locked Loop) circuit construction which includes a voltage controlled oscillator 21, a divider 22 for dividing the oscillation frequency of the voltage controlled oscillator 21 to $1/u$, a divider 23 for

further dividing the division frequency of the divider 22 to $1/v$, and a phase comparator 24 for comparing the phase of the division frequency of the divider 23 and a horizontal synchronizing frequency FH with each other and supplying the phase difference output thereof as a control input to the voltage controlled oscillator 21. The voltage controlled oscillator 21 is locked with an oscillation frequency equal to $u \times v$ times with reference to the horizontal synchronizing frequency FH to obtain a clock signal XCLK for the X direction scanning circuit 11, and the clock signal XCLK is divided to $1/u$ to obtain a clock signal YCLK for the Y direction scanning circuit 12.

However, with the clock generation circuit of the construction described above, since a large number of counters are required to construct the PLL circuit, there is a problem that, where the clock generation circuit is formed into an IC, the counters occupy a large area of the chip or consume much current. Further, where the phase difference between the clock signal XCLK and the clock signal YCLK is large, this increases the fixed pattern noise mentioned above. In order to keep the phases of the two clock signals exactly, such a countermeasure as to form

the dividers 22 and 23 from synchronous counters or to latch the outputted clock signals XCLK and YCLK to synchronize them is required.

SUMMARY OF THE INVENTION

It is an object of the present invention to provide an analog delay circuit wherein the influence of a parasitic capacitance is reduced to allow charge accumulated in a memory capacitor to be read out at a high speed.

It is another object of the present invention to provide an analog delay circuit wherein a same selection condition is applied to all memory cells without depending upon the positions of the memory cells to prevent production of fixed pattern noise.

It is a further object of the present invention to provide a clock generation circuit for a system employing a clock signal synchronized with an external reference signal wherein a PLL can be constructed without the necessity for such a circuit as a divider.

In order to attain the objects described above, according to an aspect of the present invention, there is provided an analog delay circuit, comprising an analog

value memory circuit including a plurality of memory cells each including a switch element having a terminal connected to a corresponding row line and a memory capacitor connected to the other terminal of the switch element, the memory cells being arranged in a matrix of u columns and v rows, u and v being natural numbers, v row switches arranged for the individual columns and each connected at a terminal thereof to a common input/output node and at the other terminal thereof to a terminal of the corresponding row line, a first scanning circuit for outputting column selection signals for i columns to drive the switch elements of the memory cells for the individual columns, i being equal to or larger than 1 but equal to or smaller than u , and a second scanning circuit for outputting row selection signals for j rows to drive the switch elements of the memory cells and the row switches for the individual rows, j being equal to or larger than 1 but equal to or smaller than v .

In the analog delay circuit of the construction described above, when both of the column selection signal for the i th column and the row selection signal for the j th row are rendered active, the memory cell in the i th column

and the j th row of the analog value memory circuit is selected, and the switch element of the memory cell is put into a conducting (closed) state. Simultaneously, the row switch for the j th row is selected and put into a conducting state. In this selection condition, only the switch elements of the memory cells in the j th row are connected to the input/output node, and writing/reading out of charge is performed for that one of the memory capacitors of the memory cells of the j th row which is in the i th column.

According to another aspect of the present invention, there is provided an analog delay circuit, comprising an analog value memory circuit including a plurality of memory cells each including a switch element having a terminal connected to a corresponding row line and a memory capacitor connected to the other terminal of the switch element, the memory cells being arranged in a matrix of u columns and v rows, u and v being natural numbers, a first scanning circuit for successively outputting u column selection signals to drive the switch elements of the memory cells for the individual columns, a second scanning circuit for successively outputting v row selection signals

to drive the switch elements of the memory cells for the individual rows, and a clock generation circuit for supplying a same clock signal to the first and second scanning circuits, the numbers u and v of the first and second scanning circuits being set so as to have no common divisor other than 1.

In the analog delay circuit of the construction described above, the first and second scanning circuits are driven with the same clock frequency by the same clock signal. Further, since the numbers u and v of the first and second scanning circuits do not have a common divisor other than 1, the addresses in the two X and Y directions vary for each clock when the memory cells are to be selectively scanned. Consequently, not raster scanning, but scanning of all of the memory cells is performed in accordance with a certain rule. As a result, the column selection signal and the row selection signal have a one clock width for any of the memory cells and provide a same selection condition to all of the memory cells.

According to a further aspect of the present invention, there is provided a clock generation circuit for an analog delay circuit which includes an analog value

memory circuit including a plurality of memory cells each including a switch element having a terminal connected to a corresponding row line and a memory capacitor connected to the other terminal of the switch element, the memory cells being arranged in a matrix of u columns and v rows, u and v being natural numbers, a first scanning circuit for successively outputting u column selection signals to drive the switch elements of the memory cells for the individual columns, and a second scanning circuit for successively outputting v row selection signals to drive the switch elements of the memory cells for the individual rows, the clock generation circuit supplying a same clock signal to the first and second scanning circuits, the clock generation circuit comprising a logic operation circuit for logically operating one of the column selection signals of the first scanning circuit and one of the row selection signals of the second scanning circuit, a phase comparator for comparing a phase of an output signal of the logical operation circuit and a phase of a reference signal provided from the output with each other, and a voltage controlled oscillator for receiving a comparison output of the phase comparator as a control input for an oscillation

frequency and supplying a clock signal of the oscillation frequency commonly to the first and second scanning circuits.

In the clock generation circuit of the construction described above, one of the column selection signals of the first scanning circuit and one of the row selection signals of the second scanning circuit are logically operated, and the phase of the operation output signal is compared with the phase of an external reference signal by the phase comparator. Then the oscillation frequency of the voltage controlled oscillator for producing the clock signal common to the first and second scanning circuits is controlled in response to the phase difference. Consequently, the first and second scanning circuits act as a divider which divides the oscillation frequency of the voltage controlled oscillator.

The above and other objects, features and advantages of the present invention will become apparent from the following description and the appended claims, taken in conjunction with the accompanying drawings in which like parts or elements are denoted by like reference characters.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a circuit diagram showing a basic circuit construction of an analog delay circuit as a related art;

FIG. 2 is a timing chart of operations of switches employed in the analog delay circuit of FIG. 1;

FIG. 3 is a diagrammatic view illustrating a concept of an analog delay;

FIG. 4 is a circuit diagram showing a related art of an analog delay circuit;

FIG. 5 is a circuit diagram showing an example of a related art of a construction of memory cells where a MOSFET is employed as a selection switch;

FIG. 6 is a waveform diagram illustrating operation of an analog value memory circuit according to a related art;

FIG. 7 is an enlarged waveform diagram of row and column selection signals;

FIG. 8 is a circuit diagram illustrating parasitic capacitances of a MOSFET;

FIG. 9 is a circuit diagram of an analog delay circuit of a related art which includes a parasitic capacitance;

FIG. 10 is a diagrammatic view illustrating a concept of a scanning method of a related art;

FIG. 11 is a block diagram of a clock generation circuit of a related art;

FIG. 12 is a circuit diagram of an analog memory delay circuit of a first preferred embodiment of the present invention;

FIG. 13 is a block diagram showing an example of a construction of a color signal demodulation circuit for a color television receiver of the PAL system in which a delay circuit according to the present invention is employed for a 1 H delay line and showing a second preferred embodiment of the present invention;

FIG. 14 is a detailed circuit diagram of an analog delay circuit showing a third preferred embodiment of the present invention;

FIG. 15 is a circuit diagram of an analog delay circuit showing a fourth preferred embodiment of the present invention;

FIG. 16 is a circuit diagram of an analog delay circuit showing a fifth preferred embodiment of the present invention;

FIG. 17 is a waveform diagram illustrating operation of an analog value memory circuit shown in FIG. 16;

FIG. 18 is a diagrammatic view illustrating a concept of a scanning method according to a sixth preferred embodiment of the present invention; and

FIG. 19 is a block diagram of a clock generation circuit showing a seventh preferred embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

In the following, preferred embodiments of the present invention will be described in detail with reference to the accompanying drawings. FIG. 12 is a circuit diagram showing a first preferred embodiment of the present invention. In FIG. 12, only a circuit construction of an analog value memory circuit which is essential part of the present invention is shown. The analog value memory circuit shown corresponds to the circuit of FIG. 1 which includes the N selection switches $S(N)$ and memory capacitors $C(n)$.

Referring to FIG. 12, memory cells formed from memory capacitors C_{mn} and selection switches S_{mn} connected

in series between row lines RL_n and the ground are arranged in a matrix of u columns and v rows. For those $u \cdot v$ memory capacitors C_{11} to C_{uv} , writing/reading out of charge is performed by driving control of the selection switches S_{11} to S_{uv} with column selection signals X_1 to X_u for the X direction and row selection signals Y_1 to Y_v for the Y direction. The column selection signals X_1 to X_u are outputted from an X direction scanning circuit 51, and the row selection signals Y_1 to Y_v are outputted from a Y direction scanning circuit 52. The X direction scanning circuit 51 and the Y direction scanning circuit 52 are formed, for example, from shift registers.

The analog delay circuit which includes the analog value memory circuit formed from the $u \cdot v$ memory cells (memory capacitors C_{11} to C_{uv} and selection switches S_{11} to S_{uv}) arranged two-dimensionally in a matrix has, in the present embodiment, a construction wherein row switches SY_1 to SY_v are provided for the individual rows. In particular, one terminal of each of the row switches SY_1 to SY_v is connected to a common node A serving as an input/output node while the other terminal is connected to a terminal of a corresponding one of row lines RL_1 to RL_v .

The row switches SY1 to SYv are driven by the column selection signals X1 to Xu outputted from the X direction scanning circuit 51 and the row selection signals Y1 to Yv outputted from the Y direction scanning circuit 52, respectively.

In the analog delay circuit according to the present embodiment having the construction described above, if it is assumed that the ith column and the jth row are selected now, then the column selection signal Xi outputted from the X direction scanning circuit 51 and the row selection signal Yj outputted from the Y direction scanning circuit 52 are both rendered active so that the selection switch Sij in the ith column and the jth row is selected and put into a closed (on) state. Simultaneously, from among the row switches SY1 to SYv added newly, only the row switch SYj for the jth row is selected and put into a closed state.

If the analog value memory circuit side is viewed from the node A in this selection condition, then only the jth column is connected to the node A while the remaining rows, that is, all of the first to j-1th rows and the j+1th to vth rows are disconnected from the node A. As a result,

only $1/v$ of the selection switch group (S_{11} to S_{uv}) of the u columns and the v rows is connected to the node A. In this instance, since the parasitic capacitances of the column of row switches SY_1 to SY_v increase newly, the total parasitic capacitance does not reduce simply to $1/V$, but becomes substantially equal to $1/V$. Consequently, the total parasitic capacitance decreases very much comparing with that of the related art.

As described hereinabove, since an analog value memory circuit wherein memory capacitors C_{mn} and selection switches S_{mn} for the memory capacitors C_{mn} are arranged two-dimensionally in a matrix includes row switches SY_1 to SY_v provided for the individual rows so that the selection switches S_{mn} may be selected divisionally for the individual rows, the parasitic capacitance connected to the node A is a total parasitic capacitance of the selection switches S_{mn} for one row. Consequently, the capacitance value of the parasitic capacitance can be reduced remarkably comparing with that of the related art wherein the parasitic capacitances of all of the selection switches $S(N)$ are connected to the node.

As a result, the problem of the related art that,

by an influence of the parasitic capacitance, the feedback ratio of the operational amplifier A1 (refer to FIG. 1) when charge of the memory capacitors C_{mn} is read out is reduced remarkably and this makes high speed reading difficult can be eliminated. Further, since also the amount of unnecessary charge accumulated in the parasitic capacitance almost without being delayed decreases, also disturbance to the output by such unnecessary charger can be decreased.

Subsequently, a second preferred embodiment of the present invention will be described. The analog delay circuit according to the embodiment described above is employed, for example, in a color signal demodulation circuit for a color television receiver of the PAL system. An example of a construction of the color signal demodulation circuit is shown in FIG. 13. Referring to FIG. 13, a color signal of the PAL system is supplied to a Y/C separation circuit 61, by which it is separated into a brightness (Y) signal E_r' and a chroma (C) signal. The color signal is applied also to a synchronizing separation circuit 62, by which a horizontal synchronizing signal HD is separated from it. The separated chroma signal is

inputted to one of input terminals of an adder 63 and is further inputted to the other input terminal of the adder 63 and one of input terminals of another adder 65 after it is delayed by 1 H by a 1 H delay line 64. The chroma signal is further inputted to the other input terminal of the adder 65 after it is reversed in polarity by a polarity reversal circuit 66.

The chroma signal is supplied also to a burst phase discrimination circuit 67. The burst phase discrimination circuit 67 extracts a burst signal inserted in a back porch of the horizontal synchronizing signal HD and supplies the burst signal to a subcarrier generation circuit 68 and a flipflop 69. The subcarrier generation circuit 68 produces a subcarrier of 4.43 MHz in response to the burst signal. The subcarrier is successively shifted to subcarriers having phase differences of 0 degree, 90 degrees and 180 degrees by a phase shifter 70. Then, the subcarrier of the phase difference of 0 degree and the subcarrier of the phase difference of 180 degrees are outputted alternatively by a change-over switch 71.

The change-over control of the change-over switch 71 is performed by the output of the flipflop 69 which

divides the horizontal synchronizing signal HD to $1/2$ in synchronism with the burst signal. Meanwhile, the addition outputs of the adders 63 and 65 are supplied to synchronizing detection circuits 72 and 73, respectively. The synchronizing detection circuit 72 performs detection in synchronism with the subcarrier of the phase difference of 90 degrees while the synchronizing detection circuit 73 performs detection in synchronism with the subcarrier of the phase difference of 0 degree or 180 degrees. The detection output of the synchronizing detection circuit 72 passes through a low-pass filter 74 of 1.3 MHz to make a color difference signal $E_b' - E_y'$. The detection output of the synchronizing detection circuit 73 passes through another low-pass filter 75 of 1.3 MHz to make another color difference signal $E_r' - E_y'$.

In the color signal demodulation circuit for a color television receiver of the PAL system described above, line correlation is taken using the 1 H delay line 64 to effect correction for a DP (differential phase) error, that is, a hue distortion, produced in a transmission line or in the inside of the receiver. In the color signal demodulation circuit, the analog delay circuit

according to the present embodiment is used as the 1 H delay line 64. Since the analog delay circuit according to the present embodiment includes an analog value memory circuit of the circuit construction wherein writing/reading out of charge is performed for memory capacitors arranged two-dimensionally in a matrix, it is possible to form the analog delay circuit in an integrated relationship with a color signal demodulation circuit on a chip for the color signal demodulation circuit.

It is to be noted that the application of the analog delay circuit according to the present embodiment is not limited to that wherein a color signal is delayed by 1 H in a color signal demodulation circuit for a color television receiver of the PAL system, and the analog delay circuit can be applied also to a circuit which delays a brightness signal by 1 H or which is used as a delay circuit for an audio signal.

Subsequently, a detailed embodiment of an analog value memory circuit according to a third or fourth preferred embodiment of the present invention wherein a MOSFET or a JFET is used as a switch element will be described.

FIG. 14 is a circuit diagram showing the third embodiment wherein a MOSFET is used as the switch element. Referring to FIG. 14, n-channel MOSFETs Q1 to Qv are used for the row switches SY1 to SYv, and the drains of the MOSFETs Q1 to Qv are connected to a node A while the sources are connected to one terminals of the row lines RL1 to RLv, respectively. Further, the gates of the MOSFETs Q1 to Qv are connected to row selection lines RSL1 to RSLv, respectively. Thus, row selection signals Y1 to Yv are applied to the gates of the MOSFETs Q1 to Qv via the row selection lines RSL1 to RSLv, respectively.

In the first row, the drains of n-channel MOSFETs Q11 to Qv1 as selection switches are connected to the row line RL1. One terminals of the memory capacitors C11 to Cv1 are connected to the sources of the MOSFETs Q11 to Qv1, and the other terminals of the memory capacitors C11 to Cv1 are grounded. The anodes of diodes D11 to Dv1 and one terminals of resistors R11 to Rv1 are connected to the gates of the MOSFETs Q11 to Qv1, respectively. The cathodes of the diodes D11 to Dv1 are connected to column selection lines CSL1 to CSLv, respectively, and the other terminals of the resistors R11 to Rv1 are connected to the

row selection lines RSL1 to RSLv, respectively.

Also in the second row, the drains of the MOSFETs Q12 to Qu2 are connected to the row line RL2 similarly. One terminals of the memory capacitors C12 to Cu2 are connected to the sources of the MOSFETs Q12 to Qu2, respectively, and the other terminals of the memory capacitors C12 to Cu2 are grounded. The anodes of the diodes D12 to Du2 and one terminals of the resistors R12 to Ru2 are connected to the gates of the MOSFETs Q12 to Qu2, respectively. The cathodes of the diodes D12 to Du2 are connected to the column selection lines CSL1 to CSLu, respectively, and the other terminals of the resistors R12 to Ru2 are connected to the row selection lines RSL1 to RSLv, respectively.

Further, also in the vth row, the drains of the n-channel MOSFETs Q1v to Quv are connected to the row line RLv similarly. One terminals of the memory capacitors C1v to Cuv are connected to the sources of the MOSFETs Q1v to Quv, respectively, and the other terminals of the memory capacitors C1v to Cuv are grounded. The anodes of the diodes D1v to Duv and one terminals of the resistors R1v to Ruv are connected to the gates of the MOSFETs Q1v to Quv,

respectively. The cathodes of the diodes D_{1v} to D_{uv} are connected to the column selection lines CSL_1 to CSL_u , respectively, and the other terminals of the resistors R_{1v} to R_{uv} are connected to the row selection lines RSL_1 to RSL_v , respectively.

Circuit operation of the analog delay circuit having the construction described above when, for example, the memory capacitor C_{11} is selected will be examined. In this instance, in the X direction, only the column selection signal X_1 has a high potential while the others have a low potential. Meanwhile, in the Y direction, only the row selection signal Y_1 has a high potential while the others have a low potential. Since the MOSFETs Q_{ij} which serve as selection switches are controlled at the gates thereof by signals of a matrix formed from the diodes D_{ij} and the registers R_{ij} , the gate of the MOSFET Q_{11} exhibits a high potential and the MOSFET Q_{11} is put into an on-state, and consequently, the memory capacitor C_{11} is selected.

Simultaneously with this, the MOSFET Q_1 in the row switch column of the MOSFETs Q_1 to Q_v is driven directly by the row selection signal Y_1 . Consequently, since only the

MOSFET Q1 which is a row switch for the first row is put into an on-state, only the drains of the MOSFETs Q11 to Q1l which are the selection switches of the first row are connected to the node A via the MOSFET Q1.

FIG. 15 is a circuit diagram showing the fourth embodiment wherein a JFET is used as a switch element. In the present fourth embodiment, read switches and write switches are provided as the row switches SY1 to SYv, and n-channel JFETs Q1R to QvR and Q1W to QvW are used as the switches.

In particular, referring to FIG. 15, the drains of the read JFETs Q1R to QvR are connected to a node R, and the sources of them are connected to one terminals of row lines RL1 to RLv. The anodes of diodes D1R to DvR and one terminals of resistors R1R to RvR are connected to the gates of the JFETs Q1R to QvR, respectively. The cathodes of the diodes D1R to DvR are connected to a read control line RCL, and the other terminals of the resistors R1R to RvR are connected to row selection lines RSL1 to RSLv, respectively.

Similarly, the drains of the write JFETs Q1W to QvW are connected to a node W, and the sources of them are

connected one terminals of the row lines RL1 to RLv, respectively. The anodes of diodes D1W to DvW and one terminals of resistors R1W to RvW are connected to the gates of the JFETs Q1W to QvW, respectively. The cathodes of the diodes D1W to DvW are connected to a write control line WCL, and the other terminals of the resistors R1W to RvW are connected to the row selection lines RSL1 to RSLv, respectively.

In the first row, the drains of n-channel JFETs Q11 to Qv1 which serve as selection switches are connected to the row line RL1. One terminals of the memory capacitors C11 to Cv1 are connected to the sources of the JFETs Q11 to Qv1, respectively, and the other terminals of the memory capacitors C11 to Cv1 are grounded. The anodes of the diodes D11 to Dv1 and one terminals of the resistors R11 to Rv1 are connected to the gates of the JFETs Q11 to Qv1, respectively. The cathodes of the diodes D11 to Dv1 are connected to the column selection lines CSL1 to CSLv, respectively, and the other terminals of the resistors R11 to Rv1 are connected to the row selection lines RSL1 to RSLv, respectively.

Also in the second row, the drains of n-channel

JFETs Q12 to Qu2 which serve as selection switches are connected to the row line RL2 similarly. One terminals of the memory capacitors C12 to Cu2 are connected to the sources of the JFETs Q12 to Qu2, respectively, and the other terminals of the memory capacitors C12 to Cu2 are grounded. The anodes of the diodes D12 to Du2 and one terminals of the resistors R12 to Ru2 are connected to the gates of the JFETs Q12 to Qu2, respectively. The cathodes of the diodes D12 to Du2 are connected to the column selection lines CSL1 to CSLu, respectively, and the other terminals of the resistors R12 to Ru2 are connected to the row selection lines RSL1 to RSLv, respectively.

Also in the vth row, the drains of n-channel JFETs Q1v to Quv which serve as selection switches are connected to the row line RLv similarly. One terminals of the memory capacitors Clv to Cuv are connected to the sources of the JFETs Q1v to Quv, respectively, and the other terminals of the memory capacitors Clv to Cuv are grounded. The anodes of the diodes D1v to Duv and one terminals of the resistors R1v to Ruv are connected to the gates of the JFETs Q1v to Quv, respectively. The cathodes of the diodes D1v to Duv are connected to the row selection lines CSL1 to CSLu,

respectively, and the other terminals of the resistors R_{lv} to R_{uv} are connected to the row selection lines RSL_1 to RSL_v , respectively.

Where the construction wherein the row switches SY_1 to SY_v are divided into the read JFETs Q_{lR} to Q_{vR} and the write JFETs Q_{lW} to Q_{vW} and the switches are driven by matrix driving with the write signal W and the read signal R as well as the row selection signals Y_1 to Y_v for the Y direction as described above is applied to the circuit of FIG. 1, it can be considered that it integrates the functions of the selection switches $S(N)$ for the memory capacitors $C(n)$, the write switch S_1 and the read switch S_2 .

Further, where a JFET is used for a switch element, the circuit can be produced by a bipolar process almost without any additional step. Besides, also the effect that it can be formed in the same step as that for a high current amplification ratio transistor (so-called LEC transistor) is achieved.

It is to be noted that the construction wherein the row switches SY_1 to SY_v are divided into row switches for reading out and row switches for writing is not limited to

a circuit wherein a JFET is used as a switch element, but can naturally be applied similarly to another circuit wherein a MOSFET is used as a switch element as described above in connection with the first embodiment or a further circuit wherein a bipolar transistor is used as a switch circuit.

Subsequently, an analog delay circuit according to a fifth preferred embodiment of the present invention will be described. In FIG. 16, only a circuit construction of an analog value memory circuit which is essential part of the present invention is shown. The analog value memory circuit shown corresponds to the circuit of FIG. 1 which includes the N selection switches $S(N)$ and memory capacitors $C(n)$.

Referring to FIG. 16, memory cells formed from selection switches S_{mn} and memory capacitors C_{mn} connected in series between row lines RL_n and the ground, respectively, are arranged in a matrix of u columns and v rows. In particular, in the memory cells of the first column, one terminals of selection switches S_{11} to S_{u1} are connected to an input/output node A via the row line RL_1 , and memory capacitors C_{11} to C_{u1} are connected between the

other terminals of the selection switches S11 to Su1 and the ground.

Also in the memory cells of the second row, one terminals of the selection switches S12 to Su2 are connected to the input/output node A via the row line RL2, and memory capacitors C12 to Cu2 are connected between the other terminals of the selection switches S12 to Su2 and the ground. Further, also in the memory cells of the vth row, one terminals of the selection switches S1v to Suv are connected to the input/output node A via the row line RLv, and memory capacities C1v to Cuv are connected between the other terminals of the selection switches S1v to Suv and the ground.

The $u \cdot v$ selection switches S11 to Suv can be formed from MOSFETs, JFETs or bipolar transistors similarly as in the related art. Writing/reading out of charge is performed for the $u \cdot v$ memory capacitors C11 to Cuv by driving control of the selection switches S11 to Suv with column selection signals X1 to Xu for the X direction and row selection signals Y1 to Yu for the Y direction. The column selection signals X1 to Xu are outputted from an X direction scanning circuit 81 while the row selection

signals Y1 to Yv are outputted from a Y direction scanning circuit 82.

The X direction scanning circuit 81 is formed from u stages of shift registers XSR1 to XSRu the number of which is equal to the number u of columns of the cell matrix. Meanwhile, the Y direction scanning circuit 82 is formed from v stages of shift registers YSR1 to YSRv the number of which is equal to the number v of rows of the cell matrix. A same clock signal CLK generated by a clock generation circuit 83 is supplied to the X direction scanning circuit 81 and the Y direction scanning circuit 82. In other words, the two scanning circuits 81 and 82 are driven with an equal clock frequency.

In the X direction scanning circuit 81 and the Y direction scanning circuit 82, the number u of the shift registers XSR1 to XSRu and the number v of the shift registers YSR1 to YSRv corresponding to the numbers u and v of columns and rows of the cell matrix are set so that they have no common divisor other than 1.

FIG. 17 shows operation waveforms of the analog value memory circuit of the construction described above. Referring to FIG. 17, CLK denotes a clock signal common to

the X direction scanning circuit 81 and the Y direction scanning circuit 82, X_1 , X_2 and X_u denote column selection signals for the first, second and u th columns, respectively, and Y_1 , Y_2 and Y_v are row selection signals for the first, second and v th rows, respectively. The column selection signals X_1 to X_u repetitively appear after each u clock signals CLK whereas the row selection signals Y_1 to Y_v repetitively appear after each v clock signals CLK. The column selection signal X_i and the row selection signal Y_i are clock signals shifted by one clock from the column selection signal X_{i-1} and the row selection signal Y_{i-1} , respectively.

Subsequently, a sixth embodiment of the present invention will be described.

As described above, where the X direction scanning circuit 81 and the Y direction scanning circuit 82 are driven with an equal clock frequency and the numbers u and v of the registers are set so that they have no common divisor other than 1, the addresses in both of the X and Y directions vary for every one clock. Consequently, where a cell matrix of, for example, $u = 7$ columns and $v = 5$ rows is taken as an example, the scanning is not such raster

scanning as of television scanning signals (refer to FIG. 10), but is such that all memory cells are scanned in accordance with a certain rule as seen from arrow marks in FIG. 18.

As a result, in FIG. 5 which shows the construction of a memory cell wherein a MOSFET is used as a selection switch, the column selection signal X_i and the row selection signal Y_j have a one clock width for any of the memory cells and give a same selection condition to all of the memory cells, and consequently, production of fixed pattern noise which is a subject of the related art is prevented. The essential requirement for the present embodiment is that the column number u and the row number v have no common divisor as described hereinabove, and it is necessary to select the column number u and the row number v as such. Where, for example, the case of $u = v$ is examined, it can be estimated readily that the arrangement do not function since memory cells on only diagonal lines of the cell matrix are accessed while the other memory cells are not accessed.

Subsequently, the clock generation circuit 83 for generating the clock signal CLK common to the X direction

scanning circuit 81 and the Y direction scanning circuit 82, which is a seventh preferred embodiment of the present invention, will be described. FIG. 19 is a block diagram showing the clock generation circuit according to the seventh embodiment of the present invention. It is to be noted that, in the present embodiment, an arrangement wherein the number of stages of shift registers of the X direction scanning circuit 81 is 7 ($u = 7$) and the number of stages of shift registers of the Y direction scanning circuit 82 is 5 ($v = 5$) is shown as an example.

Referring to FIG. 19, an output signal (column selection signal) of the last stage of the X direction scanning circuit 81 is inputted to one of input terminals of an AND circuit 91 while an output signal (row selection signal) of the last stage of the Y direction scanning circuit 82 is inputted to the other input terminal of the AND circuit 91. The output signal of the AND circuit 91 is supplied as a synchronizing frequency SYNC to a phase comparator 92. The phase comparator 92 compares the phase of a horizontal synchronizing frequency FH supplied thereto from the outside with the phase of the synchronizing frequency SYNC outputted from the AND circuit 91 and

supplies an output corresponding to the phase difference as a control input to a voltage controlled oscillator 93. The voltage controlled oscillator 93 has an oscillation frequency which varies in response to the phase difference output of the phase comparator 92. Then, the oscillation frequency makes the clock signal CLK common to the X direction scanning circuit 81 and the Y direction scanning circuit 82.

Meanwhile, output signals of the other stages of the X direction scanning circuit 81 than the last state are inputted to a NOR circuit 96 via OR circuits 94 and 95, and the output signal of the NOR circuit 96 is supplied as a transfer pulse signal XDRV to the first stage of the X direction scanning circuit 81. Output signals of the other stages of the Y direction scanning circuit 82 than the last stage are inputted to a NOR circuit 99 via OR circuits 97 and 98, and the output signal of the NOR circuit 99 is supplied as a transfer pulse signal YDRV to the first stage of the Y direction scanning circuit 82. Consequently, if the output signals of all stages except the last stage exhibit a low level, then a high level is returned to the first stage, and only one output from among all stages

exhibits a high level.

In the clock generation circuit according to the present embodiment having the construction described above, the output signal of the last stage of the X direction scanning circuit 81 is a pulse signal having a frequency equal to $1/u$ (in the present embodiment, $u = 7$) that of the clock signal CLK. The output of the last stage of the Y direction scanning circuit 82 is a pulse signal having a frequency equal to $1/v$ (in the present embodiment, $v = 5$) of the clock signal CLK. After each least common multiple of u and v , in particular, if u and v include no common divisor, after each $u \times v$ clocks CLK, a pulse is outputted from the AND circuit 91. After all, phase locking is established so that the voltage controlled oscillator 93 may oscillate with an oscillation frequency of $u \times v \times FH$.

Accordingly, by adopting a PLL circuit construction wherein the output of the last stage of the X direction scanning circuit 81 and the output of the last stage of the Y direction scanning circuit 82 are logically ANDed and the phase of the logical AND output is compared with the phase of the horizontal synchronizing frequency FH by the phase

comparator 92 using the logical AND output as the synchronizing frequency SYNC and then the oscillation frequency of the voltage controlled oscillator 93 is controlled in accordance with the phase difference as described above, the X direction scanning circuit 81 and the Y direction scanning circuit 82 act as a divider which divides the oscillation frequency of the voltage controlled oscillator 93, and consequently, the divider and so forth of FIG. 11 which are required by the related art become unnecessary at all. Consequently, where the present clock generation circuit is formed as an IC, the occupation area on a chip or the current consumption thereof can be reduced.

It is to be noted that, while, in the present embodiment, the output of the last stage of the X direction scanning circuit 81 and the output of the last stage of the Y direction scanning circuit 82 are logically ANDed, the outputs to be logically ANDed are not limited to the outputs of the last stages, but the outputs of any stages may be logically ANDed. Also in this instance, similar effects to those of the embodiment described above can be achieved.

Further, while the present embodiment is described by way of an example wherein u and v are set to $u = 7$ and $v = 5$, respectively, where it is used as a 1 H delay circuit for an actual color signal demodulation circuit of the PAL system, for example, u and v may be set to 11×15 . This is because a sampling frequency higher than 2 MHz is required to pass a color signal of several hundreds kHz.

As described above, according to the present invention, since an analog delay circuit including an analog value memory circuit wherein a plurality of memory cells each including a memory capacitor and a switch element are arranged in a matrix of u columns and v rows includes a plurality of row switches provided for the individual rows and each driven by a row selection signal, the parasitic capacitance connected to an input/output node in a selection condition of the memory cells is equal to a total parasitic capacitance of the switch elements for one row, and the capacitance value is reduced remarkably comparing with that of the related art. Consequently, the influence of the parasitic capacitance can be reduced and high speed reading out of charge accumulated in the memory capacitors can be achieved. Further, also disturbance by

unnecessary charge accumulated in the parasitic capacitance can be reduced.

Meanwhile, in another analog delay circuit according to the present invention, since scanning circuits for two directions are driven with a same clock frequency and the numbers of stages of the scanning circuits are set so that they have no common divisor other than 1, when memory cells are to be selectively scanned, a same selection condition can be applied to all of the memory cells without relying upon the positions of the memory cells. Consequently, production of fixed pattern noise which arises from the fact that different selection conditions are applied can be prevented.

Further, in a clock generation circuit according to the present invention, since a PLL circuit construction wherein individual output signals of two scanning circuits for two directions are logically operated and the phase of the operation output signal is compared with the phase of an external reference signal and then the oscillation frequency of a voltage controlled oscillator for generating a clock signal common to the scanning circuits for two directions is controlled in response to the phase

difference, the scanning circuits act as a divider which divides the oscillation frequency of the voltage controlled oscillator. Consequently, a divider and so forth become unnecessary and simplification in circuit construction can be anticipated.

Having now fully described the invention, it will be apparent to one of ordinary skill in the art that many changes and modifications can be made thereto without departing from the spirit and scope of the invention as set forth herein.

What Is Claimed Is:

1. An analog delay circuit, comprising:

an analog memory circuit including a plurality of memory cells each including a switch element having a terminal connected to a corresponding row line and a memory capacitor connected to a first terminal of said switch element, said memory cells being arranged in a matrix of u columns and v rows, u and v being natural numbers;

v row switches arranged for the individual columns and each connected at a terminal thereof to a common input/output node and at a second terminal thereof to a terminal of the corresponding row line;

a first scanning circuit for outputting column selection signals for i columns to drive the switch elements of the memory cells for individual columns, i being equal to or larger than 1 but equal to or smaller than u ; and

a second scanning circuit for outputting row selection signals for j rows to drive the switch elements of the memory cells and said row switches for the individual rows, j being equal to or larger than 1 but equal to or smaller than v .



2. An analog delay circuit according to claim 1, wherein each of said row switches includes a write row switch driven by a write signal and the corresponding column selection signal and a read row switch driven by a read signal and the corresponding column selection signal.

3. An analog delay circuit according to claim 1, wherein said analog delay circuit delays a color signal of a color signal demodulation signal of a television receiver by a one horizontal sweep period.

4. An analog delay circuit according to claim 1, wherein the switch elements of said analog value memory circuit and said v row switches are formed from junction type field effect transistors.

5. An analog delay circuit, comprising:

an analog memory circuit including a plurality of memory cells each including a switch element having a terminal connected to a corresponding row line and a memory capacitor connected to the other terminal of said switch element, said memory cells being arranged in a matrix of u columns and v rows, u and v being natural numbers;

a first scanning circuit for successively outputting u column selection signals to drive the switch



elements of said memory cells for the individual columns;

a second scanning circuit for successively outputting v row selection signals to drive the switch elements of said memory cells for the individual rows; and

a clock generation circuit for supplying a same clock signal to said first and second scanning circuits;

the numbers u and v of said first and second scanning circuits being set so as to have no common divisor other than 1.

6. An analog delay circuit according to claim 5, wherein said first scanning circuit includes u stages of registers, and said second scanning circuit includes v stages of shift registers.

7. An analog delay circuit according to claim 5, wherein said first and second scanning circuits scan all of said memory cells of said analog memory circuit.

8. A clock generation circuit for an analog delay circuit which includes an analog memory circuit including a plurality of memory cells each including a switch element having a first terminal connected to a corresponding row line and a memory capacitor connected to a second terminal of said switch element, said memory cells being arranged in



a matrix of u columns and v rows, u and v being natural numbers, a first scanning circuit for successively outputting u column selection signals to drive the switch elements of said memory cells for the individual columns, and a second scanning circuit for successively outputting v row selection signals to drive the switch elements of said memory cells for the individual rows, said clock generation circuit supplying a same clock signal to said first and second scanning circuits, said clock generation circuit comprising:

a logic operation circuit for logically operating one of the column selection signals of said first scanning circuit and one of the row selection signals of said second scanning circuit;

a phase comparator for comparing a phase of an output signal of said logical operation circuit and a phase of a reference signal provided from the output with each other; and

a voltage controlled oscillator for receiving a comparison output of said phase comparator as a control input for an oscillation frequency and supplying a clock signal of the oscillation frequency commonly to said first



and second scanning circuits.

9. A clock generation circuit according to claim 8, wherein said first scanning circuit includes u stages of shift registers, and said second scanning circuit includes v stages of shift registers.

10. A clock generation circuit according to claim 8, wherein said phase comparator compares a phase of an output signal of said logical operation circuit and a phase of a horizontal synchronizing signal of a video signal with each other.



52
ANALOG DELAY CIRCUIT
ABSTRACT OF THE DISCLOSURE

An analog delay circuit which includes an analog memory circuit wherein a plurality of memory cells each including a memory capacitor and a selection switch for the memory capacitor are arranged in a matrix includes row switches provided for the individual columns for individually being driven by row selection signals. A same clock signal from a clock generation circuit is supplied commonly to an X direction scanning circuit and a Y direction scanning circuit. The number of stages of registers of the X direction scanning circuit and the number of stages of registers of the Y direction scanning circuit are set so that they have no common divisor other than 1. Consequently, when the memory cells are to be selectively scanned, a same selection condition can be provided to all of the memory cells without relying upon the positions of the memory cells, and the parasitic capacitance connected to a signal write/read terminal is reduced.

Figure 12

FIG. 1 (RELATED ART)

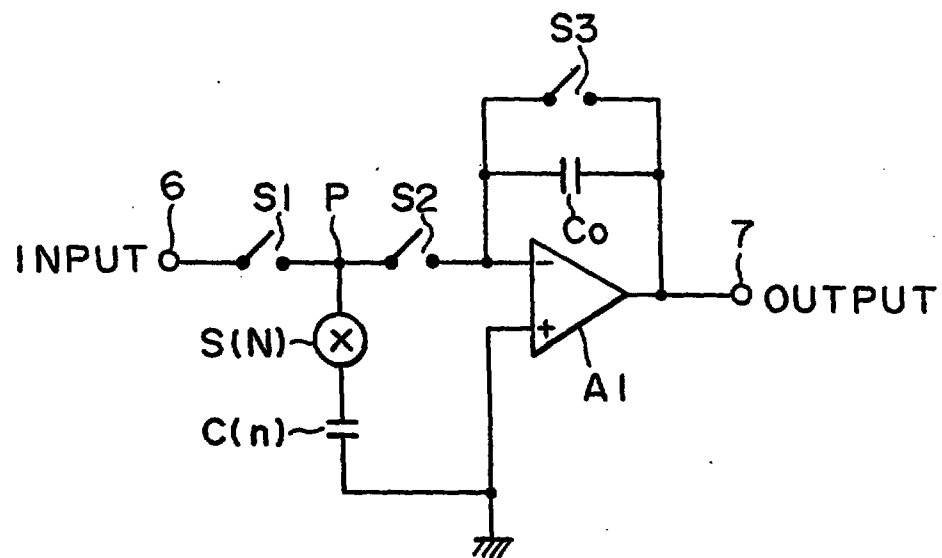


FIG. 2

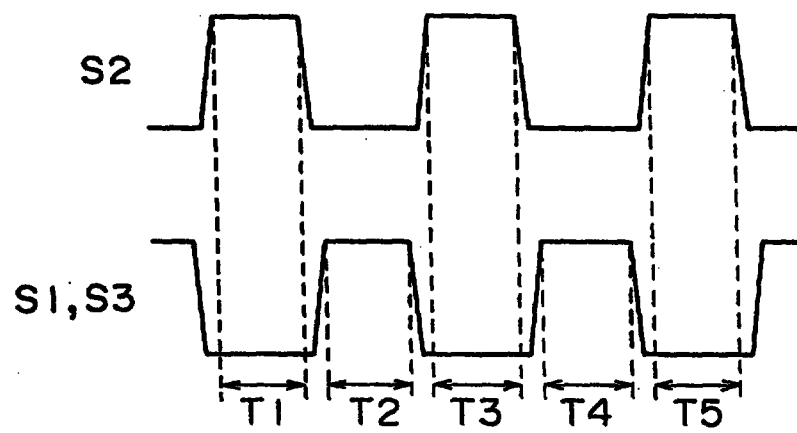


FIG. 3

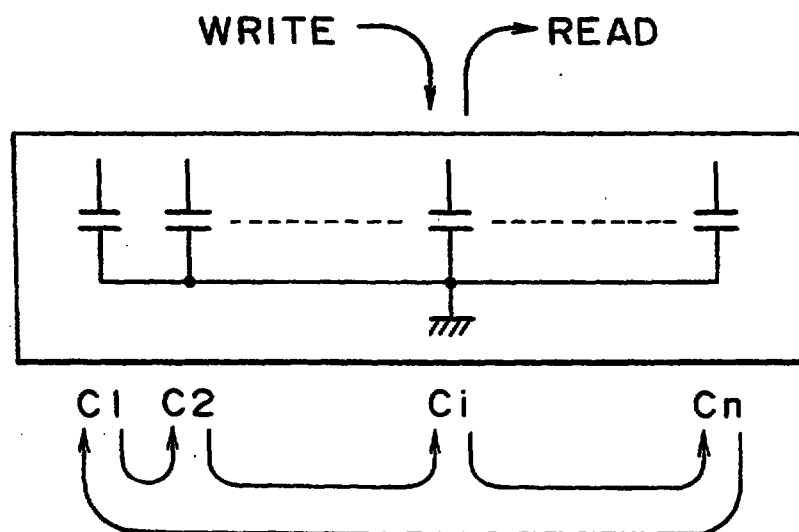


FIG. 4 (RELATED ART)^{3/13}

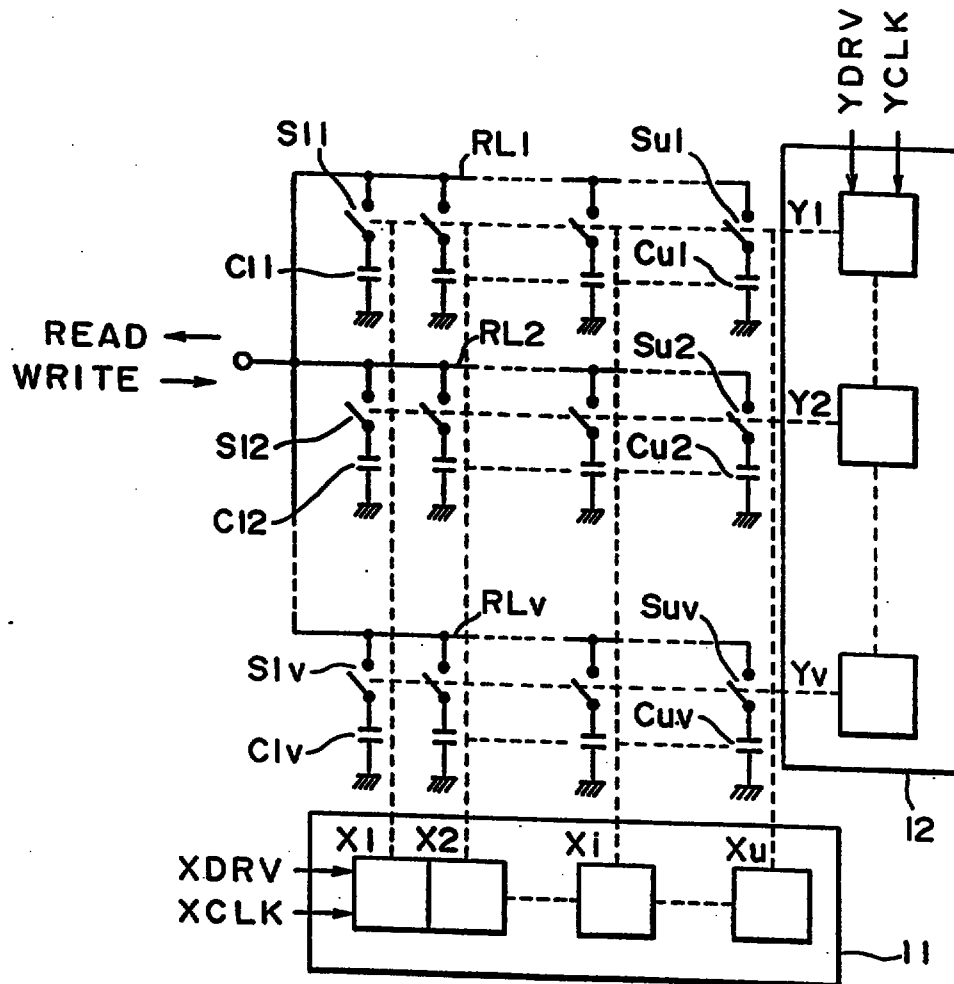


FIG. 5

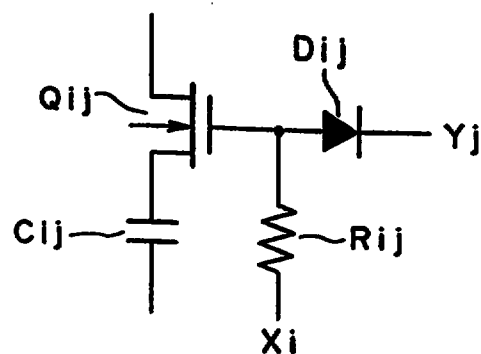


FIG. 6

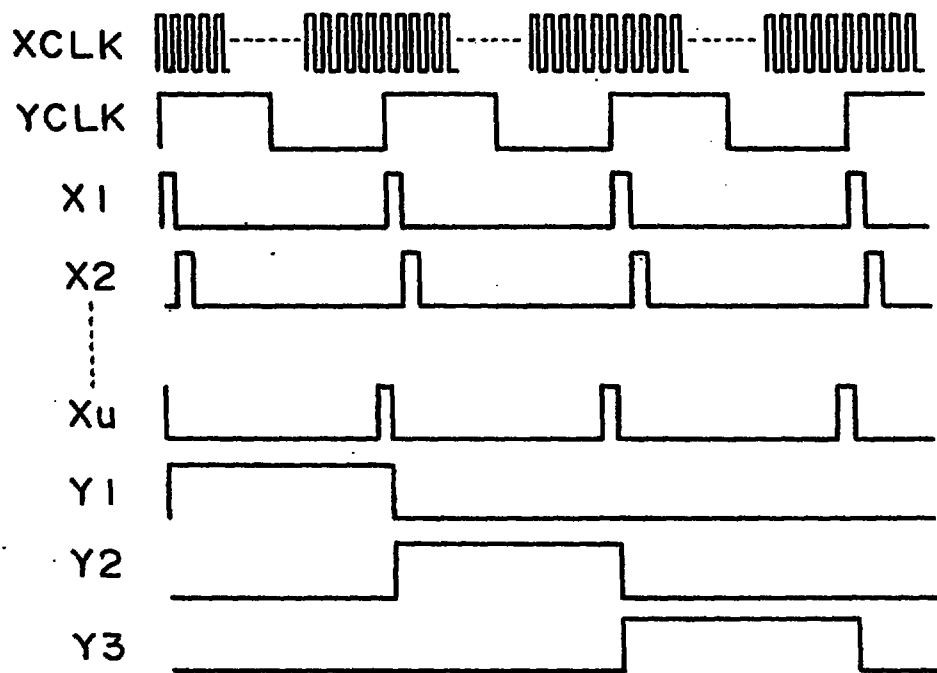


FIG. 7

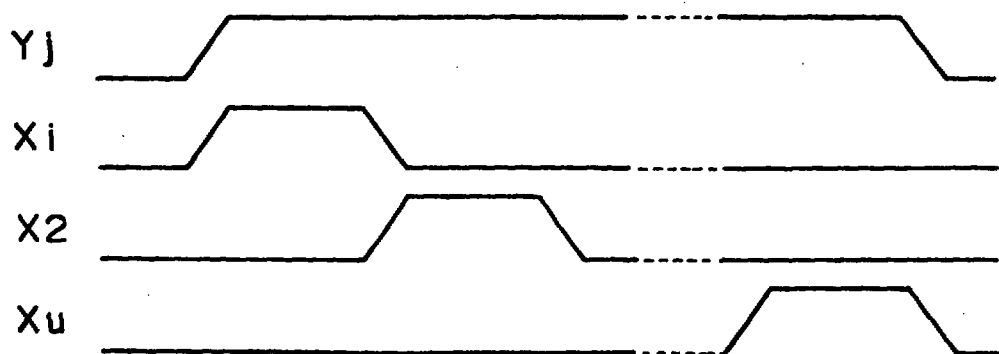


FIG. 8

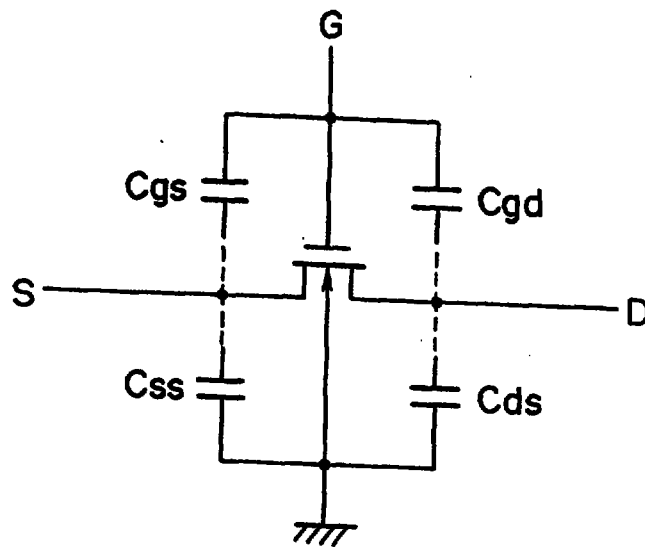


FIG. 9 (RELATED ART)

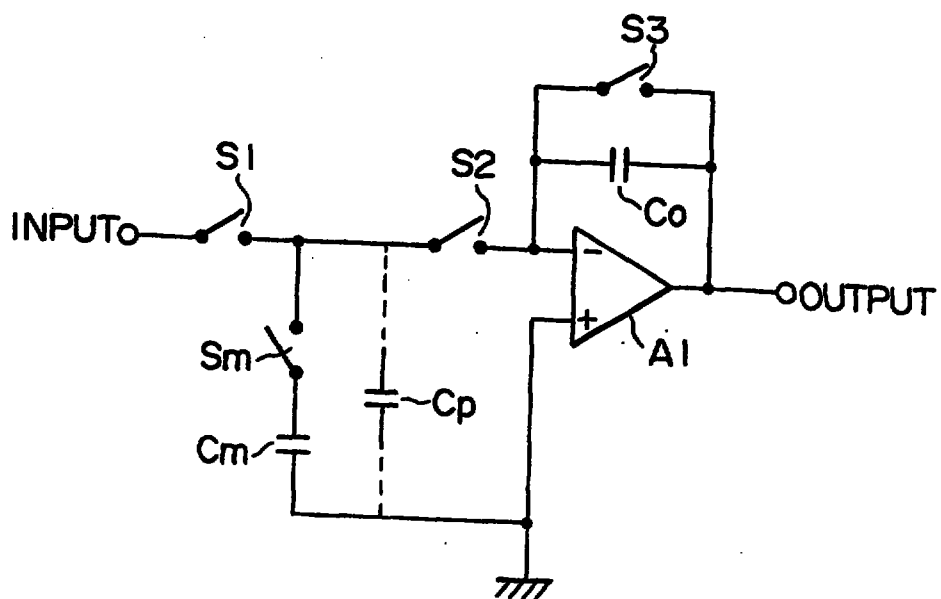


FIG. 10 (RELATED ART)

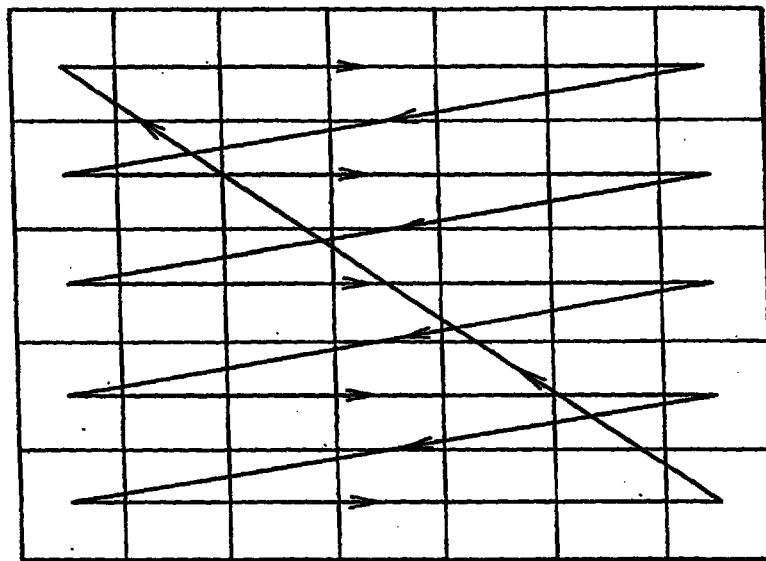


FIG. 11 (RELATED ART)

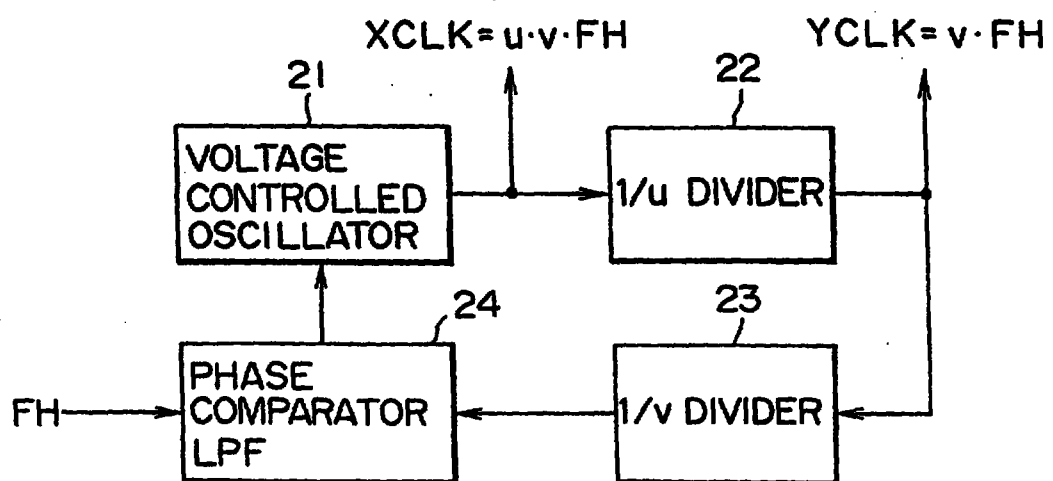


FIG. 12

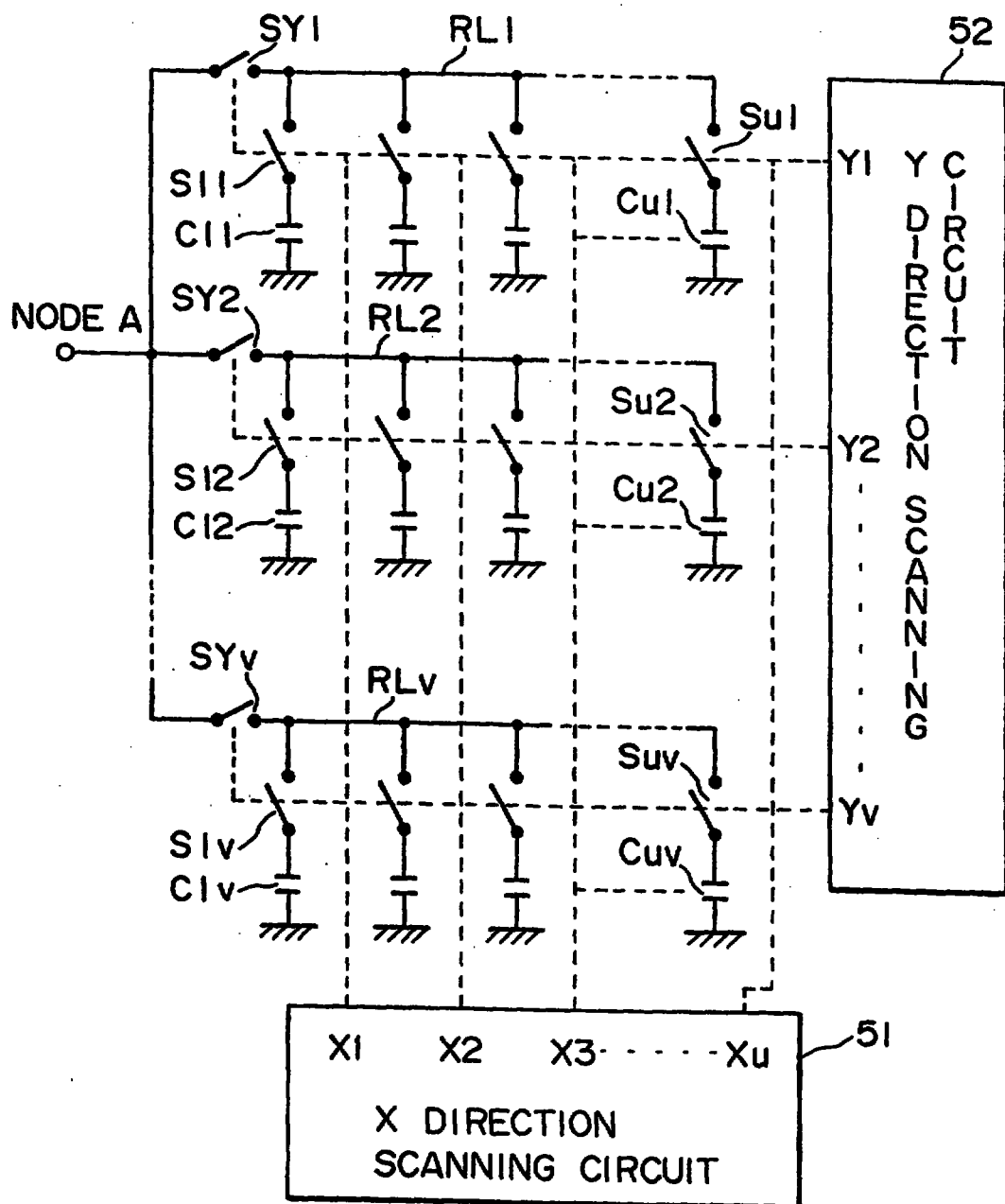


FIG. 13

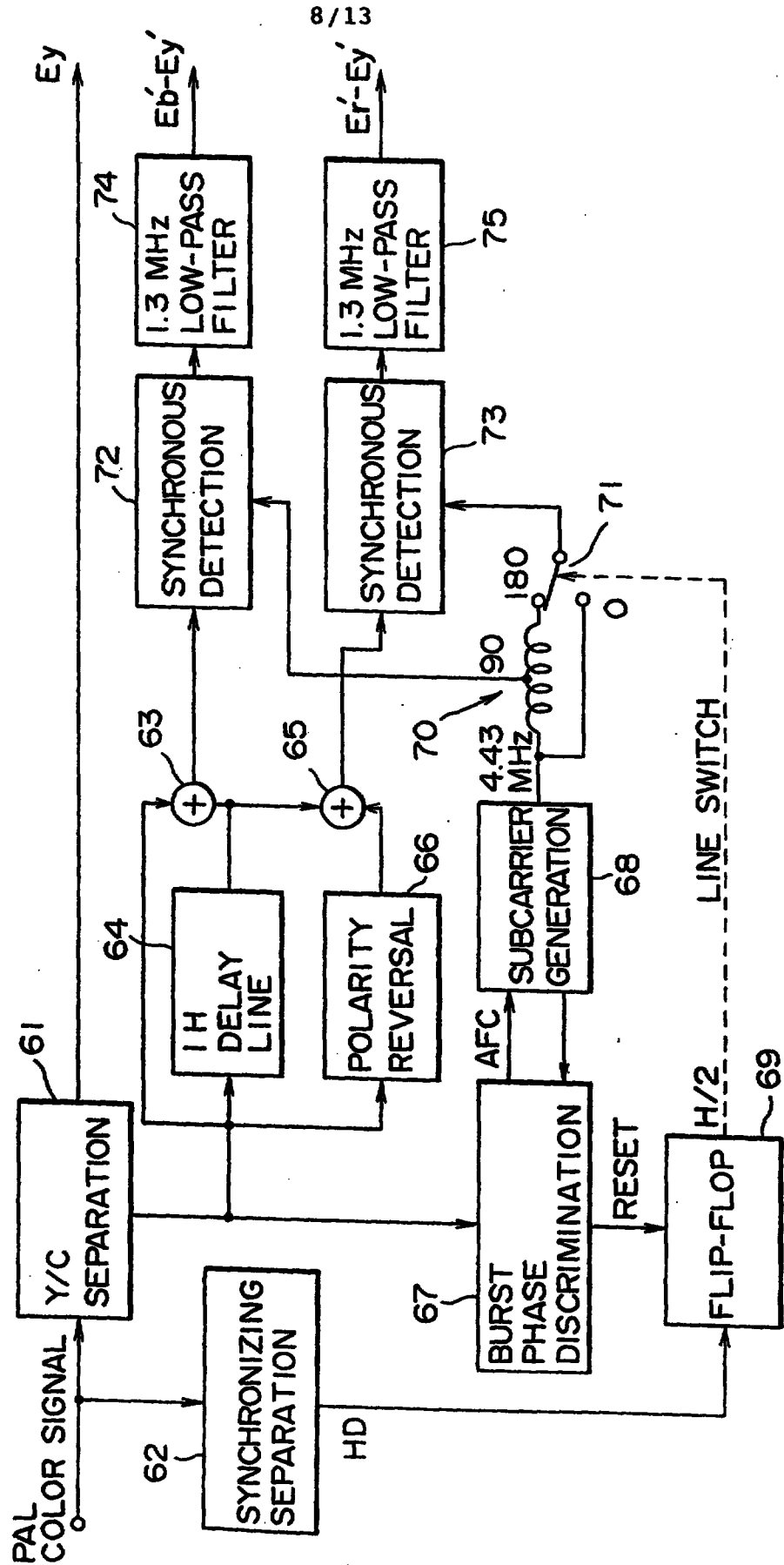


FIG. 14

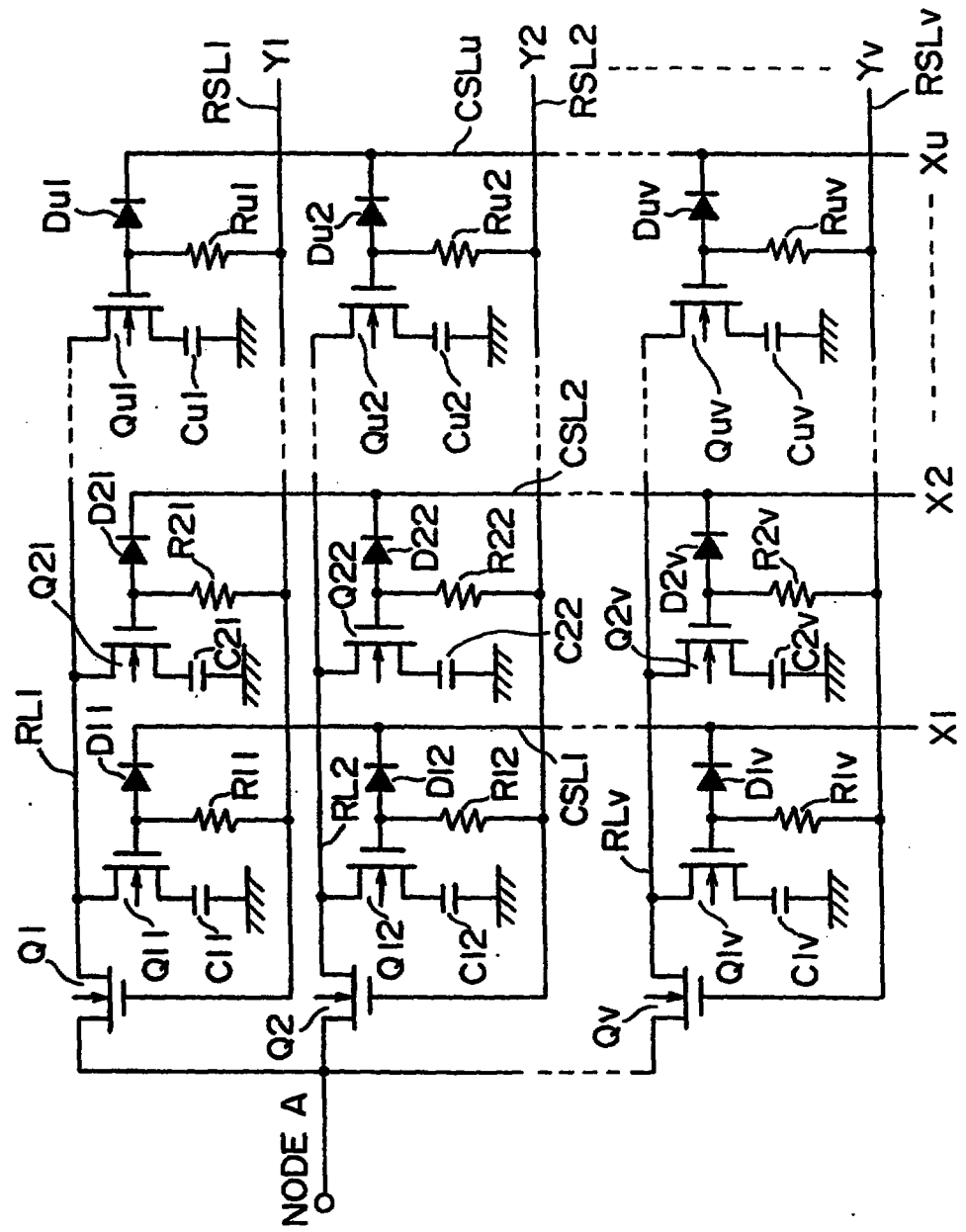


FIG. 16

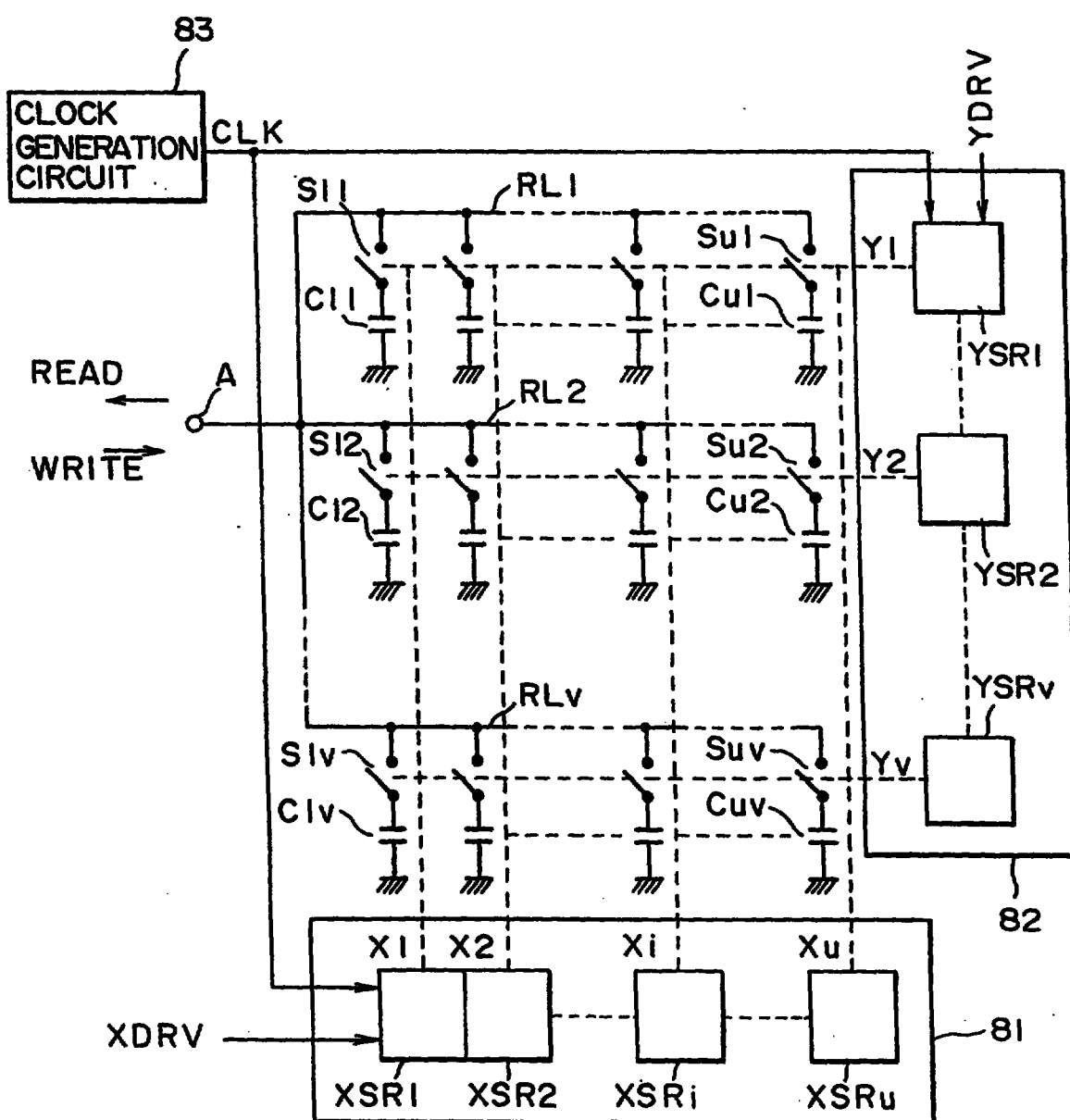


FIG. 17

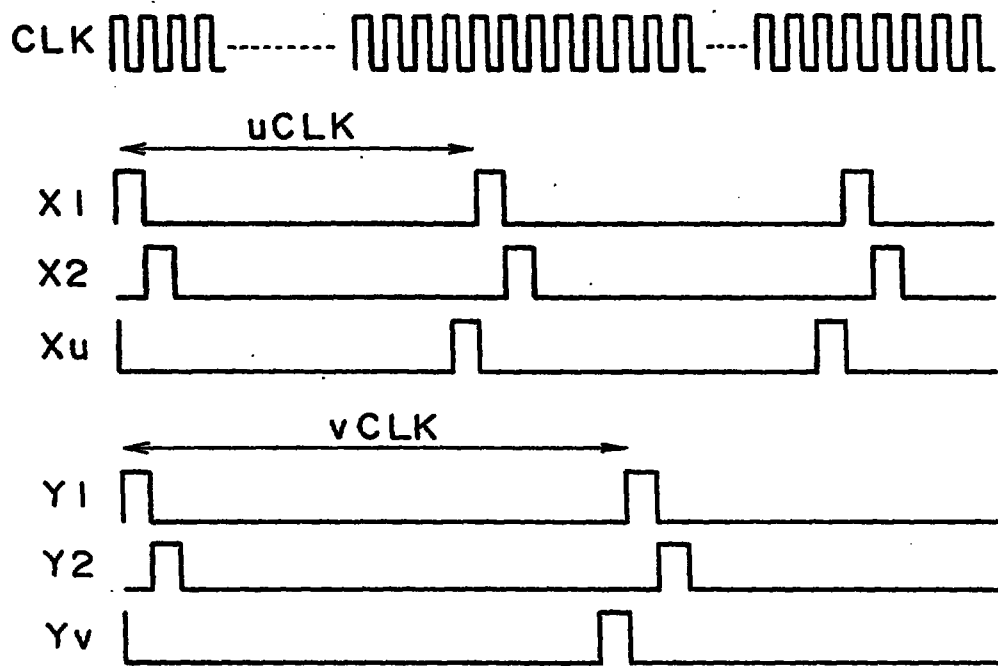


FIG. 18

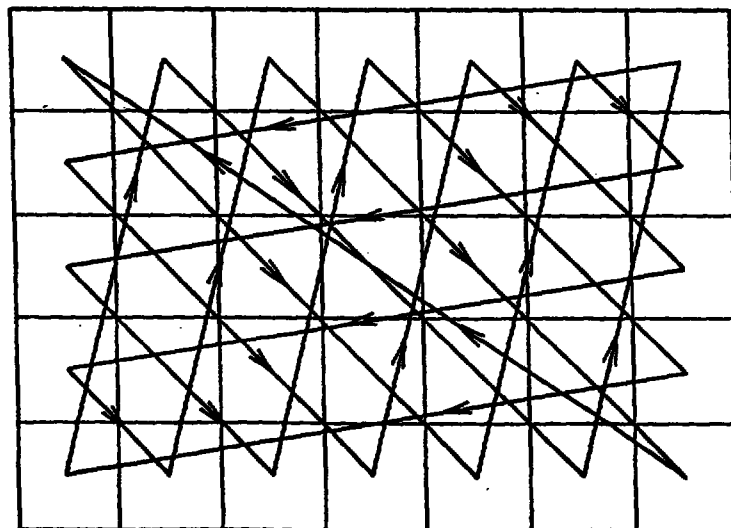
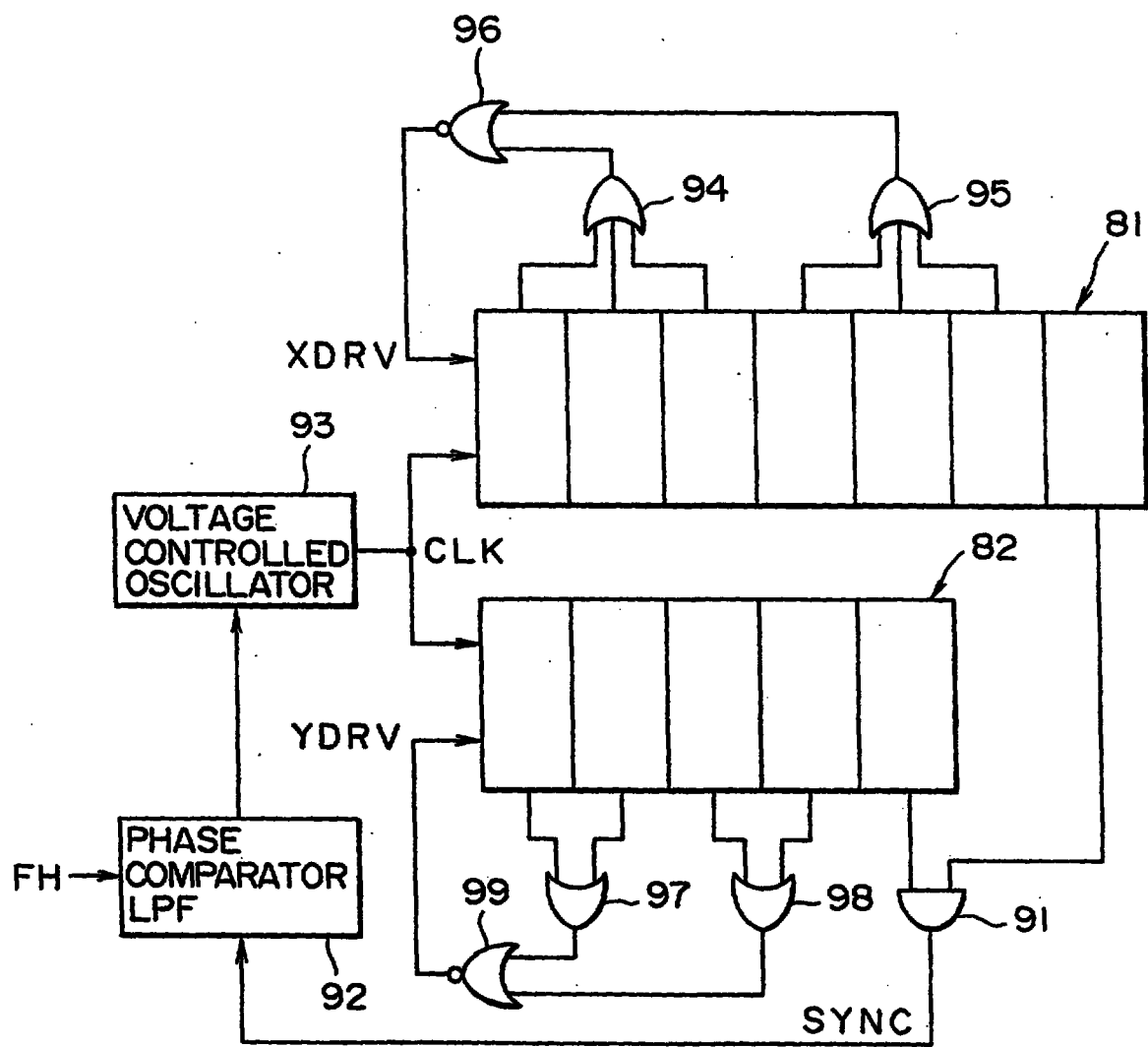


FIG. 19



81 X DIRECTION SCANNING CIRCUIT
82 Y DIRECTION SCANNING CIRCUIT